

L Number	Hits	Search Text	DB	Time stamp
11	498	(257/239).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:05
12	592	(257/310).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:10
13	510	(257/314).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:06
14	1151	(257/315).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:07
15	1470	(257/316).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:08
16	180	(438/201).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:08
17	112	(438/211).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:09
18	92	(438/212).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:09
19	1055	(438/257).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:11
20	273	(438/593).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:11
21	746	(257/321).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:12
22	167	(438/263).ccls. and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:12
28	22	@ad<=20010504 and 'Ta.sub.20.sub.5' with 'La.sub.20.sub.3'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 11:18

29	97	@ad<=20010504 and 'Ta.sub.20.sub.5' with 'ZrO.sub.2'	USPAT;	2003/06/10
			US-PGPUB;	11:17
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
30	43	@ad<=20010504 and 'Ta.sub.20.sub.5' with 'Y.sub.20.sub.3'	USPAT;	2003/06/10
			US-PGPUB;	11:17
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
31	59	@ad<=20010504 and 'Ta.sub.20.sub.5' with 'HfO.sub.2'	USPAT;	2003/06/10
			US-PGPUB;	11:39
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
36	195	@ad<=20010504 and 'silicon oxide' with 'ZrO.sub.2' with 'silicon oxide'	USPAT;	2003/06/10
			US-PGPUB;	11:42
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
37	51	@ad<=20010504 and 'silicon oxide' with 'HfO.sub.2' with 'silicon oxide'	USPAT;	2003/06/10
			US-PGPUB;	11:43
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
38	3	'flash memory' and @ad<=20010504 and 'silicon oxide' with 'ZrO.sub.2'	USPAT;	2003/06/10
			US-PGPUB;	12:53
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
43	13	'memory' and @ad<=20010504 and 'silicon oxide' with 'HfO.sub.2'	USPAT;	2003/06/10
			US-PGPUB;	13:02
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
45	1	'memory' and @ad<=20010504 and 'silicon oxide' with 'La.sub.20.sub.3'	USPAT;	2003/06/10
			US-PGPUB;	13:03
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
46	1	'memory' and @ad<=20010504 and 'silicon oxide' with 'Y.sub.20.sub.3'	USPAT;	2003/06/10
			US-PGPUB;	13:03
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	2521	((257/310) or (257/306) or (257/315)).CCLS.	USPAT;	2002/04/01
			US-PGPUB;	09:43
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	2439	((257/310) or (257/306) or (257/315)).CCLS.) and @ad<=20010504	USPAT;	2002/11/12
			US-PGPUB;	14:16
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	428	((257/310) or (257/306) or (257/315)).CCLS.) and @ad<=20010504 and 'high dielectric'	USPAT;	2002/03/29
			US-PGPUB;	11:43
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	240	((257/310) or (257/306) or (257/315)).CCLS.) and @ad<=20010504 and 'high dielectric' and 'stacked'	USPAT;	2002/03/29
			US-PGPUB;	13:17
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	450	(257/314).CCLS.	USPAT;	2002/03/29
			US-PGPUB;	13:18
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	

-	421 ((257/314).CCLS.) and @ad<=20010504	USPAT;	2002/03/29
		US-PGPUB;	13:18
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	28 (((257/314).CCLS.) and @ad<=20010504) and 'high dielectric'	USPAT;	2002/03/29
		US-PGPUB;	13:18
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	309 (((257/310) or (257/306) or (257/315)).CCLS.) and @ad<=20010504 and 'flash memory'	USPAT;	2002/03/29
		US-PGPUB;	13:42
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	6977 (257/306-330).CCLS.	USPAT;	2002/03/29
		US-PGPUB;	13:57
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	62 ((257/306-330).CCLS.) and @ad<=20010504 and 'high dielectric' and 'flash memory'	USPAT;	2002/11/12
		US-PGPUB;	14:21
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	5 821596.ap.	USPAT;	2002/03/29
		US-PGPUB;	14:15
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	3 ("4464701").PN.	USPAT;	2002/03/29
		US-PGPUB;	15:36
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	2 ("6307731").PN.	USPAT;	2002/03/29
		US-PGPUB;	15:34
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	6 109261.ap.	USPAT;	2002/03/29
		US-PGPUB;	15:36
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	129125 ("257").CLAS.	USPAT;	2002/04/01
		US-PGPUB;	10:27
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	9026 ((257/\$).CCLS.) and 'FET'	USPAT;	2002/04/01
		US-PGPUB;	08:02
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	303 (((257/\$).CCLS.) and 'FET') and 'high dielectric'	USPAT;	2002/03/29
		US-PGPUB;	16:29
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	18 (((257/\$).CCLS.) and 'FET') and 'high dielectric') and 'stacked structure'	USPAT;	2002/03/29
		US-PGPUB;	16:29
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	
-	14 (((257/\$).CCLS.) and 'FET') and 'high dielectric') and 'stacked structure') and @ad<=20010504	USPAT;	2002/03/29
		US-PGPUB;	16:30
		EPO; JPO;	
		DEPWENT;	
		IBM_TDB	

-	141	((257/\$).CCLS.) and 'FET') and 'zirconium'	USPAT;	2002/03/29
			US-PGPUB;	16:39
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	9026	((257/\$).CCLS.) and 'FET'	USPAT;	2002/04/01
			US-PGPUB;	09:04
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	1358	(257/316).CCLS.	USPAT;	2002/04/01
			US-PGPUB;	09:48
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	1351	((257/316).CCLS.) and @ad<=20010504	USPAT;	2002/04/01
			US-PGPUB;	10:18
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	392	(257/55).CCLS.	USPAT;	2002/04/01
			US-PGPUB;	10:20
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	225	(257/86).CCLS.	USPAT;	2002/04/01
			US-PGPUB;	10:20
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	129125	("257").CLAS.	USPAT;	2002/04/01
			US-PGPUB;	11:00
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	3837	((257/\$).CCLS.) and 'band gap'	USPAT;	2002/04/01
			US-PGPUB;	11:01
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	496	((257/\$).CCLS.) and 'band gap') and 'silicon oxide'	USPAT;	2002/04/01
			US-PGPUB;	10:45
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	471	((257/\$).CCLS.) and 'band gap') and 'silicon oxide') and @ad<=20010504	USPAT;	2002/04/01
			US-PGPUB;	10:46
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	38	((257/\$).CCLS.) and 'band gap' WITH 'silicon oxide'	USPAT;	2002/04/01
			US-PGPUB;	11:02
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	38	((257/\$).CCLS.) and 'band gap' WITH 'silicon oxide') and @ad<=20020504	USPAT;	2002/04/01
			US-PGPUB;	11:51
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	36	((257/\$).CCLS.) and 'band gap' WITH 'silicon oxide') and @ad<=20010504	USPAT;	2002/04/01
			US-PGPUB;	12:48
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
-	5	("5768192") or ("6011725")).PN.	USPAT;	2002/04/01
			US-PGPUB;	12:04
			EPO; JPO;	
			DEPWENT;	
			IBM_TDB	

-	1	"4173766".PN.	USPAT	2002/04/01 12:07
-	1	"4173791".PN.	USPAT	2002/04/01 12:08
-	1	"4360900".PN.	USPAT	2002/04/01 12:08
-	1	"4360900".PN.	USPAT	2002/04/01 12:09
-	1	"4380057".PN.	USPAT	2002/04/01 12:09
-	1	"4360900".PN.	USPAT	2002/04/01 12:09
-	1	"3479237".PN.	USPAT	2002/04/01 12:09
-	1	"3967310".PN.	USPAT	2002/04/01 12:09
-	1	"4527257".PN.	USPAT	2002/04/01 12:11
-	1	"4586163".PN.	USPAT	2002/04/01 12:11
-	1	"5159570".PN.	USPAT	2002/04/01 12:11
-	1	"5168334".PN.	USPAT	2002/04/01 12:13
-	1	"5214303".PN.	USPAT	2002/04/01 12:17
-	1	"5841700".PN.	USPAT	2002/04/01 12:17
-	1	"5825686".PN.	USPAT	2002/04/01 12:18
-	1	"5793079".PN.	USPAT	2002/04/01 12:18
-	1	"5768192".PN.	USPAT	2002/04/01 12:18
-	1	"5168334".PN.	USPAT	2002/04/01 12:18
-	24579	'flash memory' and @ad<=20010504	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/06/10 11:49
-	241	('flash memory' and @ad<=20010504) and 'high dielectric'	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2002/11/12 14:20
-	6468	((257/239) or (257/314-326) or (257/295) or (257/298) or (438/201) or (438/257) or (438/212) or (438/593)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2002/11/12 14:24
-	139	'flash memory' and @ad<=20010504 and 'oxide' same 'high dielectric' same 'oxide'	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2002/11/12 15:21
-	22	@ad<=20010504 and 'gate insulator' with 'oxide' with 'high dielectric' with 'oxide'	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2002/11/12 15:11
-	83	'flash memory' and @ad<=20010504 and 'oxide' with 'high dielectric' with 'oxide'	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2002/11/12 15:25
-	14	'flash memory' and @ad<=20010504 and 'oxide' with 'trapping layer' with 'oxide'	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2002/11/12 15:28

-	0	'flash memory' and @ad<=20010504 and 'trapping layer' with 'Ta.sub.2.O.sub.5'	USPAT;	2002/11/12
			US-PGPUB;	15:30
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	0	'flash memory' and @ad<=20010504 and 'trapping layer' with 'high dielectric'	USPAT;	2002/11/12
			US-PGPUB;	15:31
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	1	'flash memory' and @ad<=20010504 and 'trapping layer' same 'high dielectric'	USPAT;	2002/11/12
			US-PGPUB;	15:30
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	0	@ad<=20010504 and 'trapping layer' same 'Ta.sub.2O.sub.5'	USPAT;	2002/11/12
			US-PGPUB;	15:37
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	446	@ad<=20010504 and 'trapping layer'	USPAT;	2002/11/12
			US-PGPUB;	15:38
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	0	(@ad<=20010504 and 'trapping layer') and 'high k'	USPAT;	2002/11/12
			US-PGPUB;	15:39
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	11	(@ad<=20010504 and 'trapping layer') and 'high dielectric'	USPAT;	2002/11/12
			US-PGPUB;	15:45
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	0	(@ad<=20010504 and 'trapping layer') and 'Ti.sub.2O'	USPAT;	2002/11/12
			US-PGPUB;	15:45
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	17	(@ad<=20010504 and 'trapping layer') and 'TiO.sub.2'	USPAT;	2002/11/12
			US-PGPUB;	15:46
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	1	'flash memory' and @ad<=20010504 and 'trapping layer' and 'TiO.sub.2'	USPAT;	2002/11/12
			US-PGPUB;	15:51
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	0	'EPROM' and @ad<=20010504 and 'trapping layer' and 'TiO.sub.2'	USPAT;	2002/11/13
			US-PGPUB;	08:19
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	31	'EPROM' and @ad<=20010504 and 'trapping layer'	USPAT;	2002/11/13
			US-PGPUB;	08:26
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	214	'EPROM' and @ad<=20010504 and 'high dielectric'	USPAT;	2002/11/13
			US-PGPUB;	08:35
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	
-	2	('EPROM' and @ad<=20010504 and 'high dielectric') and charge adj1 trap	USPAT;	2002/11/13
			US-PGPUB;	08:35
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	

-	6 (257/316).cccls. and @ad<=20010504 and 'high k'	USPAT; 2003/06/10 US-PGPUB; 11:04 EPC; JPO; DEPWENT; IBM_TLB
-	9 (257/315).cccls. and @ad<=20010504 and 'high k'	USPAT; 2002/11/13 US-PGPUB; 08:50 EPC; JPO; DEPWENT; IBM_TLB
-	5 (257/314).cccls. and @ad<=20010504 and 'high k'	USPAT; 2002/11/13 US-PGPUB; 08:50 EPC; JPO; DEPWENT; IBM_TLB